Y 371	Hits	Search Text	DB	Time stamp
L Number	41	(257/645).CCLS.	USPAT;	2002/05/13 17:26
1	41	(237) 043) : 0015 :	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
2	2	((257/645).CCLS.) and trap with (density	USPAT;	2002/05/13 16:45
4		carrier impurity holes electron) same	US-PGPUB;	
	1	nitride	EPO; JPO;	
		11101140	DERWENT;	
			IBM TDB	
3	182	(257/\$).ccls. and trap with (density	USPAT;	2002/05/13 17:02
		carrier impurity holes electron) same	US-PGPUB;	
		nitride	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	154	control with gate and trap with (density	USPAT;	2002/05/13 17:01
•		carrier impurity holes electron) same	US-PGPUB;	
		nitride	EPO; JPO;	
•	1		DERWENT;	
			IBM_TDB	(05 (10 17 00
5	83	(control with gate and trap with (density	USPAT;	2002/05/13 17:02
		carrier impurity holes electron) same	US-PGPUB;	
		nitride) not ((257/\$).ccls. and trap with	EPO; JPO;	
		(density carrier impurity holes electron)	DERWENT;	
		same nitride)	IBM_TDB	2002/05/12 17:07
6	3	5907183.pn.	USPAT;	2002/05/13 17:27
			US-PGPUB;	<u> </u>
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	2002/05/13 17:27
7	3	5731238.pn.	USPAT;	2002/05/13 17:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
		the second state and the secon	USPAT;	2002/05/13 10:55
-	18	insulation with layer with trap with	US-PGPUB;	2002/03/13 10:33
		density	EPO; JPO;	
			DERWENT;	
			IBM TDB	
		sa	USPAT;	2002/05/11 12:02
-	5	floating adj gate with trap adj density	US-PGPUB;	2002,00, == ====
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
		("4154873" "4331709" "4447272"	USPAT	2002/05/10 16:23
_	6	"5010024" "5017979" "5019533").PN.		
	135		USPAT;	2002/05/11 12:20
-	135	insulating insulator flating adj gate	US-PGPUB;	
		control adj gate ONO NON) with trap adj	EPO; JPO;	
		density	DERWENT;	
		densicy	IBM TDB	
_	26	silicon adj nitride with trap adj density	USPAT;	2002/05/11 14:38
-	26	31110011 adj literiae with trap adj achorej	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	8	silicon adj nitride with trap adj density	USPAT;	2002/05/11 14:38
-	•	same hydrogen	US-PGPUB;	
		Jame Hydrogen	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3	5731238.pn.	USPAT;	2002/05/13 11:02
-	1	5/51250.pm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1		1	IBM TDB	1

				2002/05/13 11:04
	174 l		US-PGPUB;	
ļ			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/05/13 11:03
		(hydrogen with NON with insulating) and	002227	2002/03/13 11111
	2	floating with gate	US-PGPUB; EPO; JPO;	
		lioacing was 5	DERWENT;	
			IBM TDB	
	!	and and	USPAT;	2002/05/13 11:07
	31	(hydrogen with NON with insulating) and	US-PGPUB;	
		nitride with hydrogen	EPO; JPO;	
			DERWENT;	1
			IBM_TDB	7000 (05 (13 11:18
		silicon with nitride with hydrogen and	USPAT;	2002/05/13 11:18
	82	floating with gate	US-PGPUB;	
		floating with gate	EPO; JPO;	
			DERWENT;	
			IBM_TDB USPAT	2002/05/13 11:14
	7	("4688078" "4788082" "5256205"	USPAI	2002, 011
-	1	"5356672" "5356673" "5368697		
		"5403399").PN.	USPAT;	2002/05/13 11:39
_	3		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2000/05/12 11:10
	Ì	TARROW TINDEN	USPAT	2002/05/13 11:18 2002/05/13 11:43
-	1	5483097.URPN. silicon adj nitride wiht density	USPAT;	2002/05/13 11.43
-	1009419	silicon adj micride wind and	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB USPAT;	2002/05/13 11:40
	33960	(silicon adj nitride wiht density) and	US-PGPUB;	2002,
-	33300	(257/\$).ccls.	EPO; JPO;	
			DERWENT;	
			IBM TDB	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
		in the density) and	USPAT;	2002/05/13 11:41
_	43257	(silicon adj nitride wiht density) and inter ajd layer and floating with gate and	US-PGPUB;	
		inter and layer and riodering was s		
		(257/\$).ccls.	DERWENT;	
			IBM_TDB	2002/05/13 11:43
	95	(silicon adj nitride wiht density) and	USPĀT; US-PGPUB;	2002/03/13 12310
_	95	inter adj layer and floating with gate and	EDO: TDO:	
		(257/\$).ccls.	EPO; JPO; DERWENT;	
		\	IBM TDB	
1			USPAT;	2002/05/13 11:43
_	249	silicon adj nitride with density	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/13 11.4
		(silicon adj nitride with density) and	USPAT;	2002/05/13 11:4
-		1 (silicon adj nitride with denoty) inter adj layer and floating with gate an	d US-PGPUB;	
		(257/\$).ccls.		
		(231/4).0013.	DERWENT;	1
Ì			IBM_TDB USPAT;	2002/05/13 11:4
		2 (silicon adj nitride with density) and	US-PGPUB	
-		floating with gate and (257/\$).ccls.	EPO; JPO	
	1		DERWENT;	
			IBM TDB	
			USPAT;	2002/05/13 12:1
_	1	silicon adj nitride adj density	US-PGPUB	
			EPO; JPO);
1			DERWENT;	
			IBM TDB	1

		thermal with nitr\$8 same trap adj density	USPAT; 2002/05/13 12:12
-	8	thermal with niciso same clap adj demotor	US-PGPUB;
			EPO; JPO;
			DERWENT;
[IBM_TDB
_	8	thermal with nitr\$ same trap adj density	USPAT; 2002/05/13 12:13
1	_		US-PGPUB;
			EPO; JPO; DERWENT;
			IBM TDB
		a the transfer game transadi	USPAT; 2002/05/13 12:14
-	0	thermal with nitrization same trap adj	US-PGPUB;
	į	density	EPO; JPO;
			DERWENT;
			IBM_TDB
_	0	thermal with nitrization and trap adj	USPAT; 2002/05/13 12:14
		density	US-PGPUB;
		-	EPO; JPO;
			DERWENT; IBM TDB
			USPAT; 2002/05/13 16:41
-	30	thermal with nitrization	US-PGPUB;
			EPO; JPO;
			DERWENT;
			IBM TDB